MSKSEMI 美森科













ESD

TVS

TSS

MOV

GDT

PLED

SS8050-MS

Product specification





TRANSISTOR (NPN)

FEATURES

• Complimentary to SS8550-MS

Reference News

PACKAGE OUTLINE		MARKING		
	1. BASE 2. EMITTER 3.COLLECTOR	Y1		
SOT-23				

MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
Vсво	Collector-Base Voltage	40	V
VCEO	Collector-Emitter Voltage	25	V
VEBO	Emitter-Base Voltage	5	V
lc	Collector Current	1.5	А
Pc	Collector Power Dissipation	300	mW
R _{ØJA}	Thermal Resistance From Junction To Ambient	417	°C/W
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55 ~ +150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

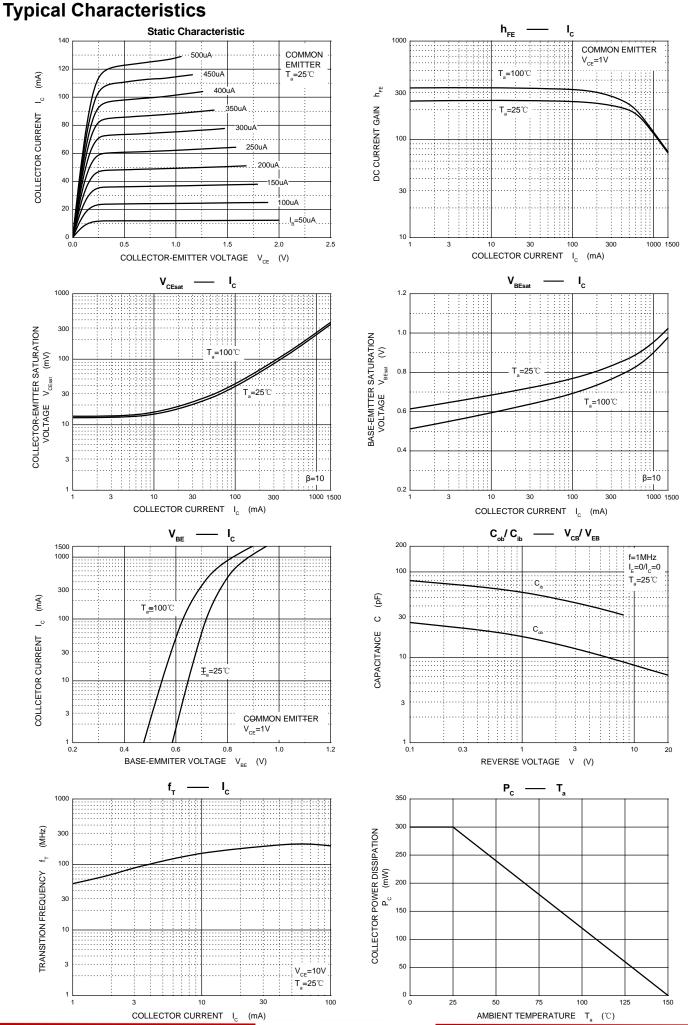
Parameter	Symbol	Test conditions	Min	Тур	Мах	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	lc= 100μΑ, I _E =0	40			V
Collector-emitter breakdown voltage	V(BR)CEO	l _C = 0.1mA, I _B =0	25			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =100μΑ, I _C =0	5			V
Collector cut-off current	Ісво	V_{CB} =40V, I _E =0			0.1	μΑ
Collector cut-off current	ICEO	V_{CE} =20V, I _E =0			0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} = 5V, I _C =0			0.1	μA
	hfe(1)	V _{CE} =1V, I _C = 100mA	120		400	
DC current gain	hfe(2)	V _{CE} =1V, I _C = 800mA	40			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =800mA, I _B = 80mA			0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	lc=800mA, I _B = 80mA			1.2	V
Transition frequency	f⊤	V _{CE} =10V, Ic= 50mA f=30MHz	100			MHz

CLASSIFICATION OF hFE(1)

Rank	L	н	J
Range	120-200	200-350	300-400



SS8050-MS

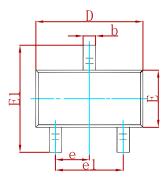


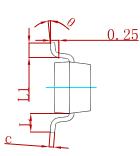
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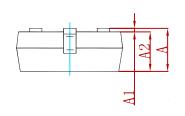
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PACKAGE MECHANICAL DATA

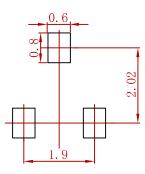






Symbol	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
А	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.037	7 TYP	
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022	2 REF	
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

Suggested Pad Layout



Note: 1.Controlling dimension:in millimeters. 2.General tolerance:± 0.05mm. 3.The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
SS8050-MS	SOT-23	3000



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